

CMOSH-3
SURFACE MOUNT
SILICON SCHOTTKY DIODE

ULTRAmiTM



SOD-523 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMOSH-3 type is a Silicon Schottky diode, epoxy molded in an ULTRAmiTM surface mount package, designed for fast switching applications requiring a low forward voltage drop.

MARKING CODE: 53

MAXIMUM RATINGS: (T_A=25°C)

Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, t_p=10ms
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{RRM} 30
I_F 100
I_{FRM} 350
I_{FSM} 750
P_D 250
T_J, T_{stg} -65 to +150
θ_{JA} 500

UNITS

V
mA
mA
mA
mW
°C
°C/W

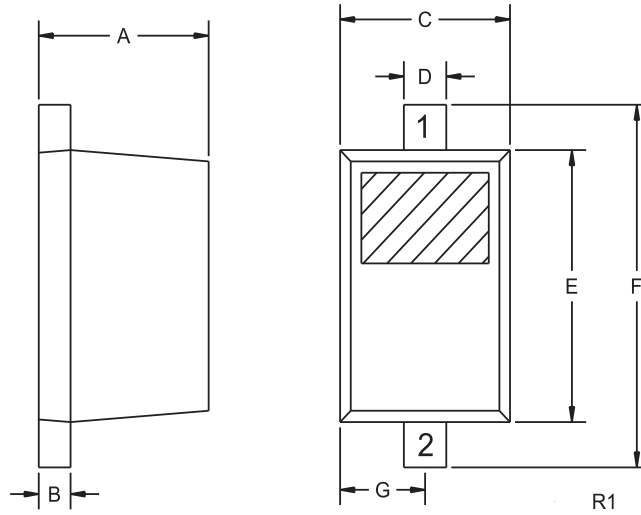
ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _R	V _R =25V		90	500	nA
I _R	V _R =25V, T _A =100°C		25	100	μA
BV _R	I _R =100μA	30			V
V _F	I _F =2.0mA		0.29	0.33	V
V _F	I _F =15mA		0.40	0.45	V
V _F	I _F =100mA		0.74	1.00	V
C _T	V _R =1.0V, f=1.0MHz		7.0		pF
t _{rr}	I _F =I _R =10mA, I _{rr} =1.0mA, R _L =100Ω			5.0	ns

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SOD-523 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Cathode
- 2) Anode

MARKING CODE: 53

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.020	0.031	0.50	0.80
B	0.004	0.008	0.10	0.20
C	0.028	0.035	0.70	0.90
D	0.008	0.011	0.20	0.28
E	0.039	0.055	1.00	1.40
F	0.055	0.071	1.40	1.80
G	0.016		0.40	

SOD-523 (REV: R1)

R3 (25-January 2010)